

Supplementary Information

Van der Waals heterostructure of graphene and Germanane: Tuning the ohmic contact by electrostatic gating and mechanical strain

A. Bafekry,^{1, *} S. Karbasizadeh,² M. Fara ji,³ A. Bagheri Khatibani,⁴
I. Abdolhosseini Sarsari,² D. Gogova,⁵ and M. Ghergherehchi⁶,

¹Department of Radiation Application, Shahid Beheshti University, 19839 69411 Tehran, Iran

²Department of Physics, Isfahan University of Technology, Isfahan, 84156-83111, Iran

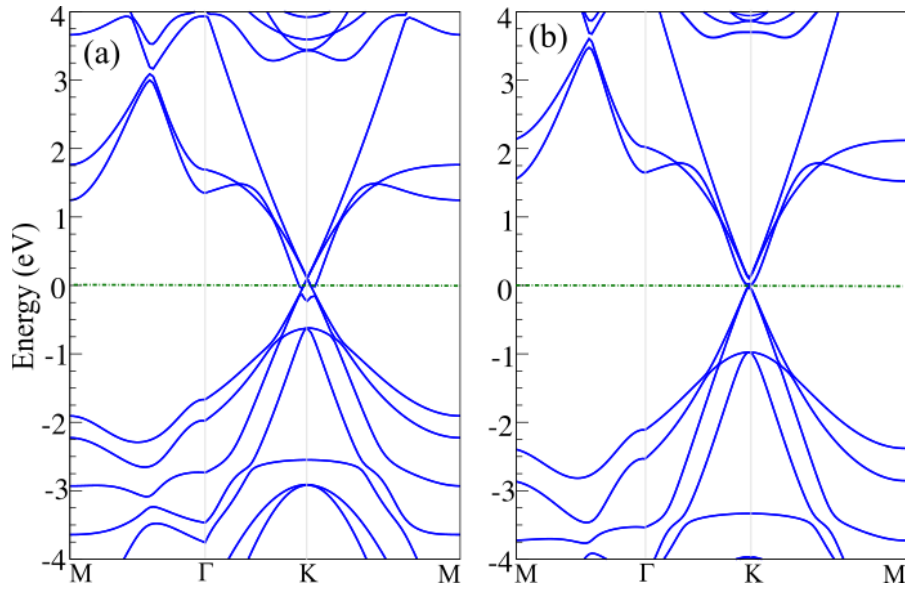
³Micro and Nanotechnology Graduate Program, TOBB University of Economics and Technology, Sogutozu Caddesi No 43 Sogutozu, 06560, Ankara, Turkey

⁴Nano Research Lab, Lahijan Branch, Islamic Azad University, Lahijan, Iran

⁵Department of Physics, Chemistry and Biology, Linkoping University, 58183 Linkoping, Sweden

⁶Department of Electrical and Computer Engineering, Sungkyunkwan University, 16419 Suwon, Korea

Email: bafekry.asad@gmail.com



FigS1. Electronic band structure of GeH/Gr HTS with considering (a) PBE and (b) HSE06 functionals. Zero is set to Fermi-level.

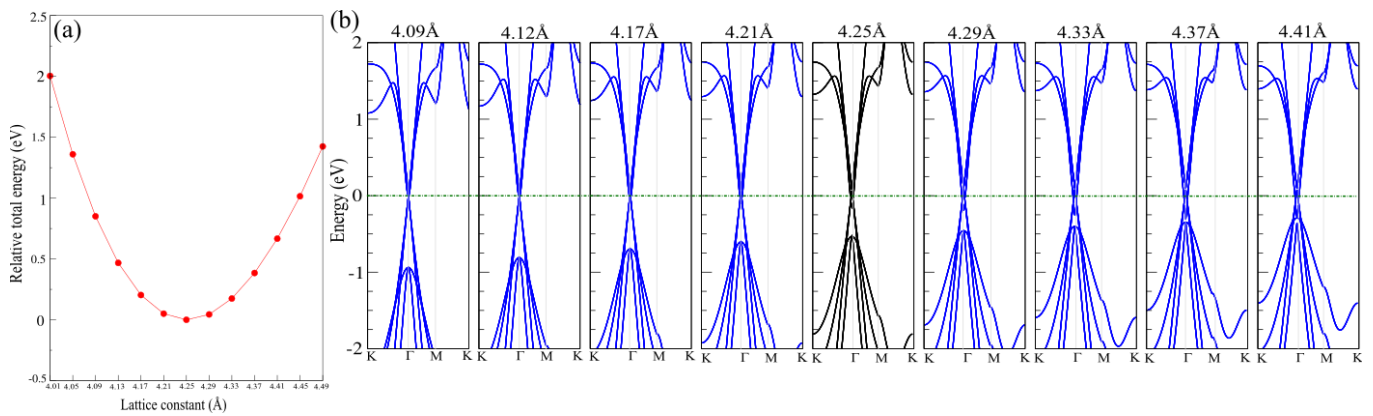


Fig. S2. (a) relative total energies for different lattice constants. (b) Band structures of the GeH/Gr HTS with varying lattice constants. This figure shows that changing the constant, whether it is increasing or decreasing it compared to the most stable value, has small to zero effects on the bands .of the HTS

